

A STATISTICAL STUDY OF THE UV Si IV RESONANCE LINES' PARAMETERS IN 20 Be STARS

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Many hot emission stars present absorption lines with complex profiles. These complex profiles are explained if we consider that they result from a number of Satellite Absorption Components (SACs), which are created in different density regions. Here, we study the complex profiles of the Si IV resonance lines $\lambda\lambda$ 1393.755, 1402.77 Å in the spectra of 20 Be stars, using the Gauss-Rotation model (GR model), with which we also calculate the kinematical and some physical parameters of the regions where these lines are created, such as the absorbed or emitted energy, the column density and the optical depth.